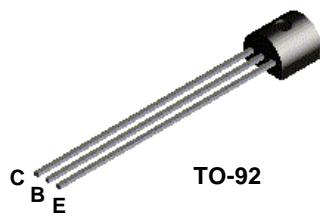


# N

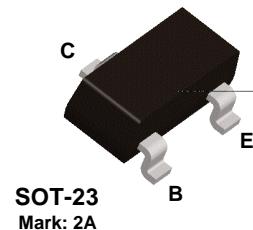
**Discrete POWER & Signal  
Technologies**

**2N3906 / MMBT3906 / MMPQ3906 / PZT3906**

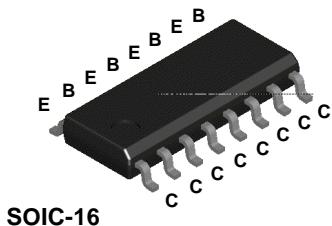
**2N3906**



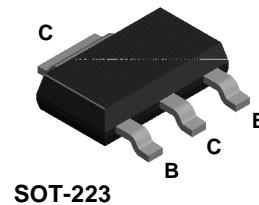
**MMBT3906**



**MMPQ3906**



**PZT3906**



## **PNP General Purpose Amplifier**

This device is designed for general purpose amplifier and switching applications at collector currents of 10 µA to 100 mA. Sourced from Process 66.

### **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CBO</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**NOTES:**

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

**PNP General Purpose Amplifier**

(continued)

**Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
<b>OFF CHARACTERISTICS</b>					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \mu\text{A}, I_E = 0$	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		V
$I_{BL}$	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{BE} = 3.0 \text{ V}$		50	nA
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{BE} = 3.0 \text{ V}$		50	nA

**ON CHARACTERISTICS**

$h_{FE}$	DC Current Gain *	$I_C = 0.1 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 1.0 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_C = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$	60 80 100 60 30	300	
$V_{CE(\text{sat})}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.25 0.4	V
$V_{BE(\text{sat})}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.65	0.85 0.95	V

**SMALL SIGNAL CHARACTERISTICS**

$f_T$	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V}, f = 100 \text{ MHz}$	250		MHz
$C_{obo}$	Output Capacitance	$V_{CB} = 5.0 \text{ V}, I_E = 0, f = 100 \text{ kHz}$		4.5	pF
$C_{ibo}$	Input Capacitance	$V_{EB} = 0.5 \text{ V}, I_C = 0, f = 100 \text{ kHz}$		10.0	pF
NF	Noise Figure (except MMPQ3906)	$I_C = 100 \mu\text{A}, V_{CE} = 5.0 \text{ V}, R_S = 1.0 \text{k}\Omega, f = 10 \text{ Hz to } 15.7 \text{ kHz}$		4.0	dB

**SWITCHING CHARACTERISTICS (except MMPQ3906)**

$t_d$	Delay Time	$V_{CC} = 3.0 \text{ V}, V_{BE} = 0.5 \text{ V},$		35	ns
$t_r$	Rise Time	$I_C = 10 \text{ mA}, I_{B1} = 1.0 \text{ mA}$		35	ns
$t_s$	Storage Time	$V_{CC} = 3.0 \text{ V}, I_C = 10 \text{ mA}$		225	ns
$t_f$	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$		75	ns

\* Pulse Test: Pulse Width  $\leq 300 \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ **Spice Model**

PNP (Is=1.41f Xti=3 Eg=1.11 Vaf=18.7 Bf=180.7 Ne=1.5 Ise=0 Ikf=80m Xtb=1.5 Br=4.977 Nc=2 Isc=0 Ikr=0 Rc=2.5 Cjc=9.728p Mjc=.5776 Vjc=.75 Fc=.5 Cje=8.063p Mje=.3677 Vje=.75 Tr=33.42n Tf=179.3p Itf=.4 Vtf=4 Xtf=6 Rb=10)

**PNP General Purpose Amplifier**

(continued)

**Thermal Characteristics**

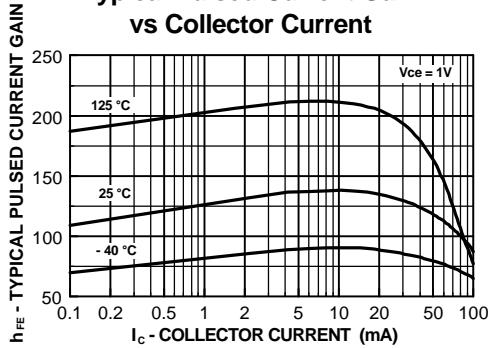
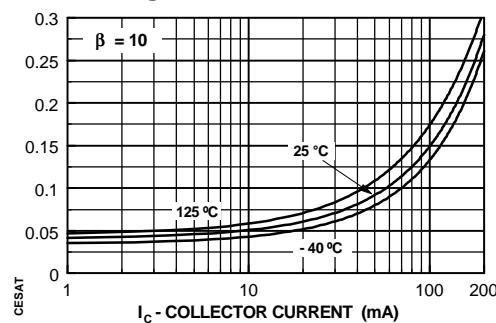
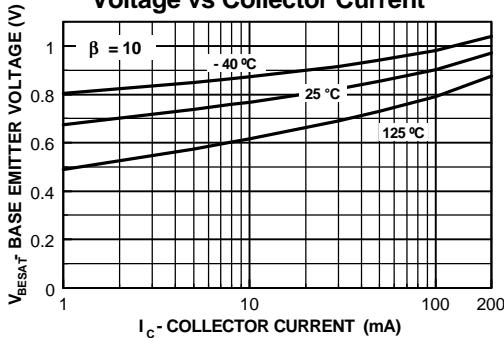
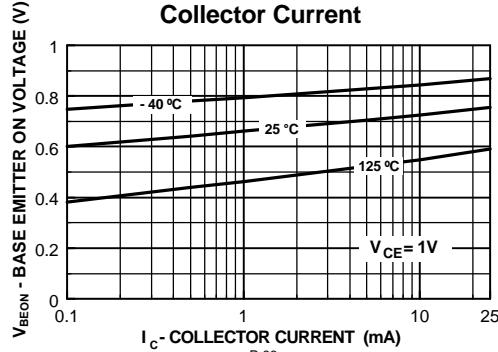
TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N3906	*PZT3906	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	1,000 8.0	mW mW/°C
R <sub>qJC</sub>	Thermal Resistance, Junction to Case	83.3		°C/W
R <sub>qJA</sub>	Thermal Resistance, Junction to Ambient	200	125	°C/W

Symbol	Characteristic	Max		Units
		**MMBT3906	MMPQ3906	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	1,000 8.0	mW mW/°C
R <sub>qJA</sub>	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	357	125 240	°C/W °C/W °C/W

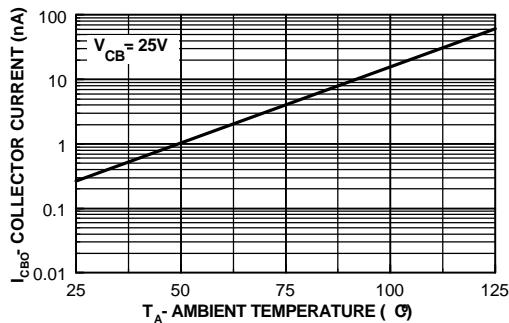
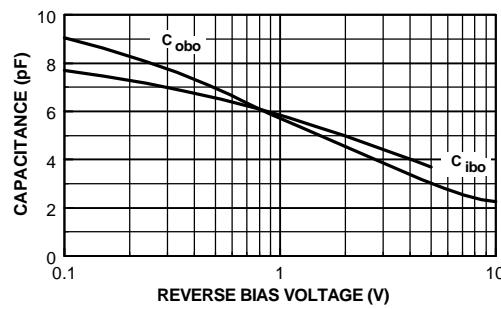
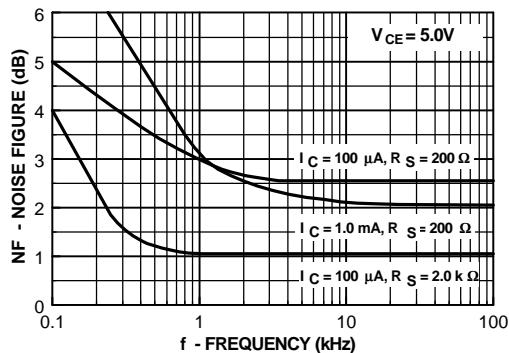
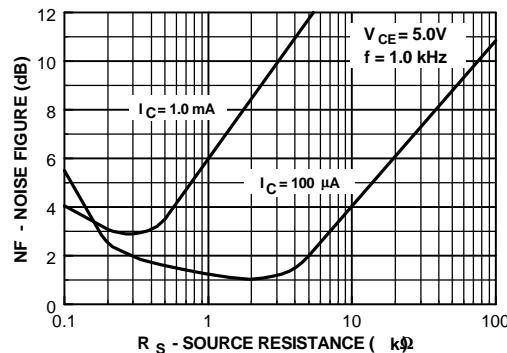
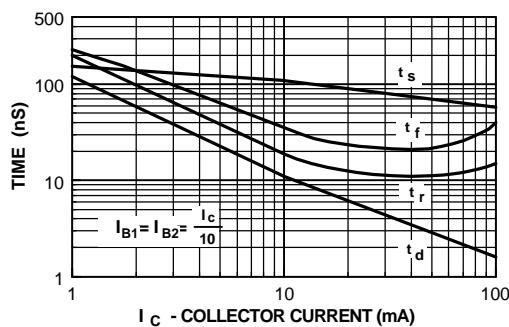
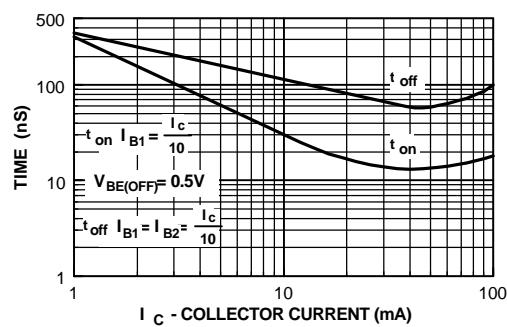
\* Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm

\*\* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

**Typical Characteristics****Typical Pulsed Current Gain  
vs Collector Current****Collector-Emitter Saturation  
Voltage vs Collector Current****Base-Emitter Saturation  
Voltage vs Collector Current****Base Emitter ON Voltage vs  
Collector Current**

**PNP General Purpose Amplifier**

(continued)

**Typical Characteristics** (continued)**Collector-Cutoff Current vs. Ambient Temperature****Common-Base Open Circuit Input and Output Capacitance vs Reverse Bias Voltage****Noise Figure vs Frequency****Noise Figure vs Source Resistance****Switching Times vs Collector Current****Turn On and Turn Off Times vs Collector Current**

## PNP General Purpose Amplifier

(continued)

### Typical Characteristics (continued)

